



## CTL190NS10-T52

### N-Channel Enhancement MOSFET

#### Features

- Drain-Source Breakdown Voltage  $V_{DSS}$  100V
- Drain-Source On-Resistance  
 $R_{DS(ON)}$  65m $\Omega$ , at  $V_{GS}= 10V, I_D= 12A$   
 $R_{DS(ON)}$  75m $\Omega$ , at  $V_{GS}= 5V, I_D= 12A$
- Continuous Drain Current at  $T_C=25^\circ C I_D = 19A$
- Advanced high cell density Trench Technology
- RoHS Compliance & Halogen Free

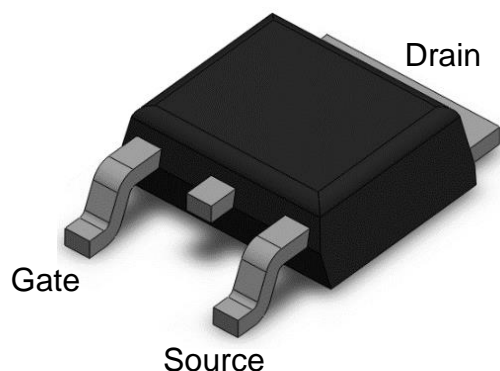
#### Description

The CTL190NS10-T52 is the N-Channel logic enhancement mode power field effect transistors are produced using high cell density, DMOS trench technology. This high density process is especially tailored to minimize on-state resistance. These devices are particularly suited for low voltage application.

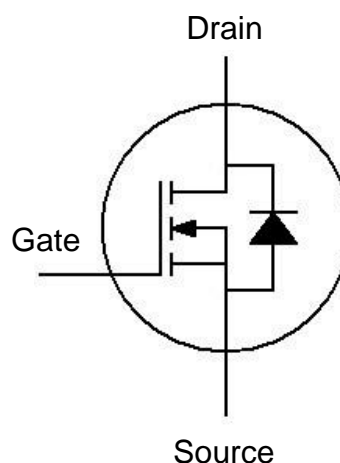
#### Applications

- DC/DC Converter
- Load Switch
- LCD Display inverter

#### Package Outline



#### Schematic





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#### Absolute Maximum Rating at 25°C

Symbol	Parameters	Test Conditions	Min	Note
V <sub>DS</sub>	Drain-Source Voltage	100	V	
V <sub>GS</sub>	Gate-Source Voltage	±20	V	
I <sub>D</sub>	Continuous Drain Current @T <sub>c</sub> =25°C	19	A	1
I <sub>DM</sub>	Pulsed Drain Current	76	A	1
P <sub>D</sub>	Total Power Dissipation @T <sub>c</sub> =25°C	45	W	2
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C	
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 150	°C	

#### Thermal Characteristics

Symbol	Parameters	Test Conditions	Min	Typ	Max	Units	Notes
R <sub>θJC</sub>	Thermal Resistance Junction-Case		--	--	2.8	°C/W	1,4



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### Electrical Characteristics $T_A = 25^\circ\text{C}$ (unless otherwise specified)

#### Static Characteristics

Symbol	Parameters	Test Conditions	Min	Typ	Max	Units	Notes
$B_{V_{DS}}$	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	100	-	-	V	
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS} = 80V, V_{GS} = 0V$	-	-	1	$\mu A$	
$I_{GSS}$	Gate-Source Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	$\pm 100$	nA	

#### On Characteristics

Symbol	Parameters	Test Conditions	Min	Typ	Max	Units	Notes
$R_{DS(ON)}$	Drain-Source On-Resistance	$V_{GS} = 10V, I_D = 12A$	-	65	78	m $\Omega$	3
		$V_{GS} = 5V, I_D = 12A$	-	75	98	m $\Omega$	3
$V_{GS(th)}$	Gate-Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\mu A$	1.0	-	2.5	V	3

#### Dynamic Characteristics

Symbol	Parameters	Test Conditions	Min	Typ	Max	Units	Notes
$C_{ISS}$	Input Capacitance	$V_{GS} = 0V,$ $V_{DS} = 15V$ $f = 1MHz$	-	1120	-	pF	
$C_{OSS}$	Output Capacitance		-	83	-		
$C_{RSS}$	Reverse Transfer Capacitance		-	54	-		

#### Switching Characteristics

Symbol	Parameters	Test Conditions	Min	Typ	Max	Units	Notes
$T_{D(ON)}$	Turn-On Delay Time	$V_{DS} = 50V, R_G = 4.7\Omega$ $V_{GS} = 5V, R_L = 3.3\Omega$	-	25.5	-	ns	
$T_R$	Rise Time		-	429	-		
$T_{D(OFF)}$	Turn-Off Delay Time		-	45.5	-		
$T_F$	Fall Time		-	91.2	-		
$Q_G$	Total Gate Charge	$V_{DS} = 80V,$ $V_{GS} = 5V,$ $I_D = 15.7A$	-	16.8	-	nC	
$Q_{GS}$	Gate-Source Charge		-	7.3	-		
$Q_{GD}$	Gate-Drain (Miller) Charge		-	9.7	-		



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### Drain-Source Diode Characteristics

Symbol	Parameters	Test Conditions	Min	Typ	Max	Units	Notes
$V_{SD}$	Body Diode Forward Voltage	$V_{GS} = 0V, I_{SD} = 1A$	-	-	1.3	V	1
$I_{SD}$	Body Diode Continuous Current		-	-	1	A	1

Note:

1. The power dissipation is limited by 150°C junction temperature.
2. The data tested by pulsed , pulse width  $\leq 300\mu s$  , duty cycle  $\leq 2\%$
3. Thermal Resistance follow JESD51-3.



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### Typical Characteristic Curves

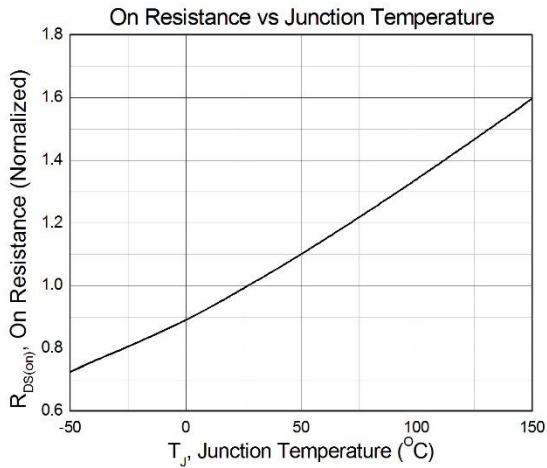


Figure 1

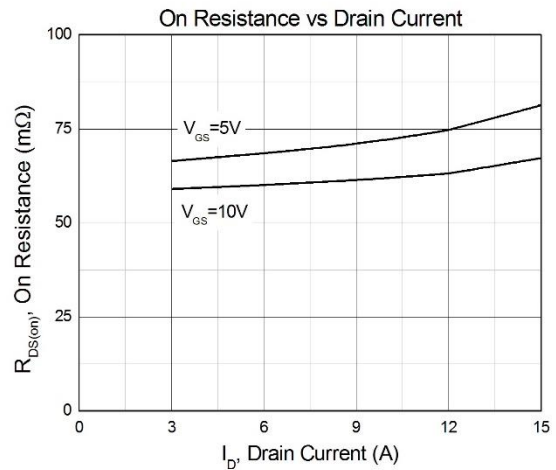


Figure 2

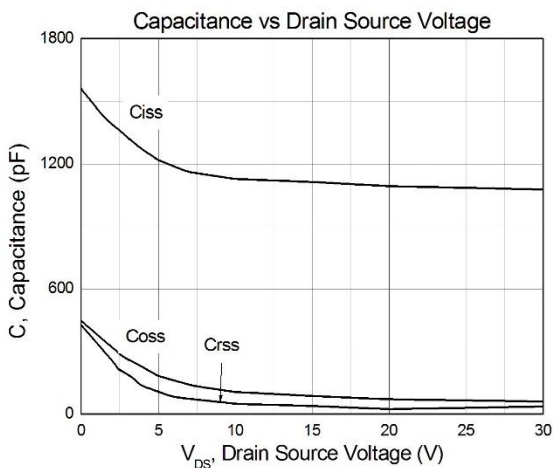


Figure 3

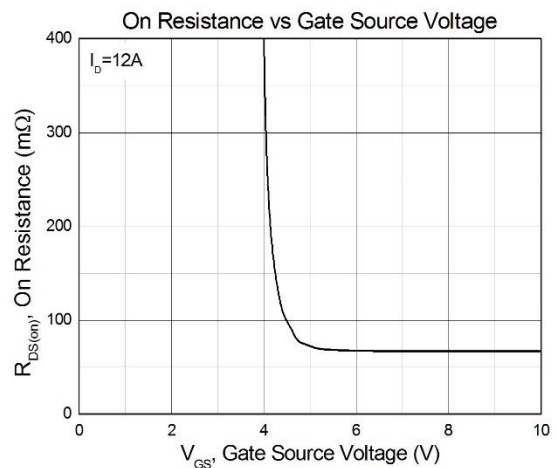


Figure 4

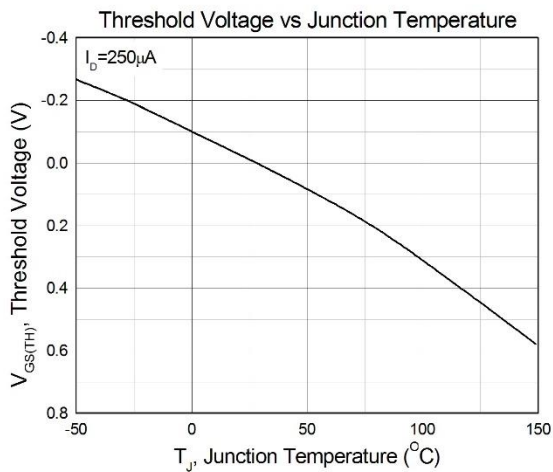


Figure 5

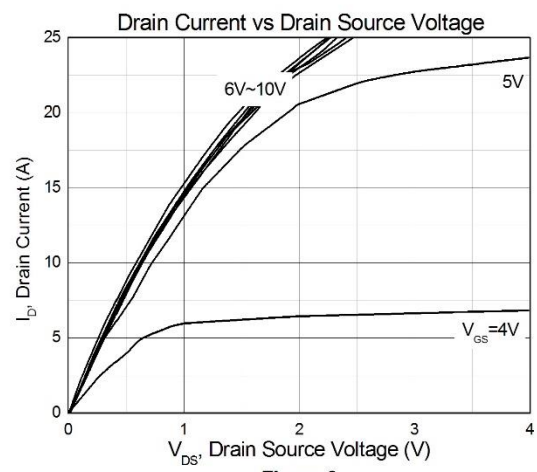


Figure 6



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## N-Channel Enhancement MOSFET

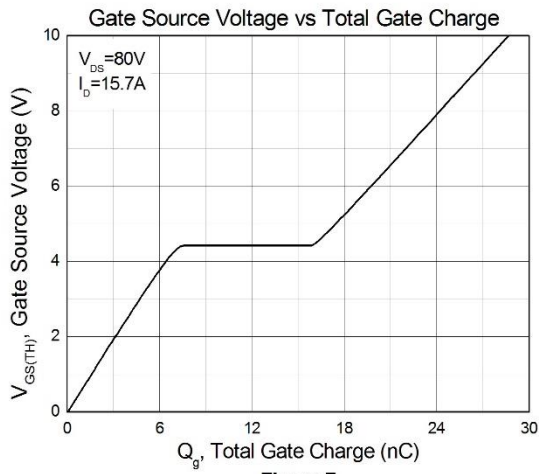


Figure 7

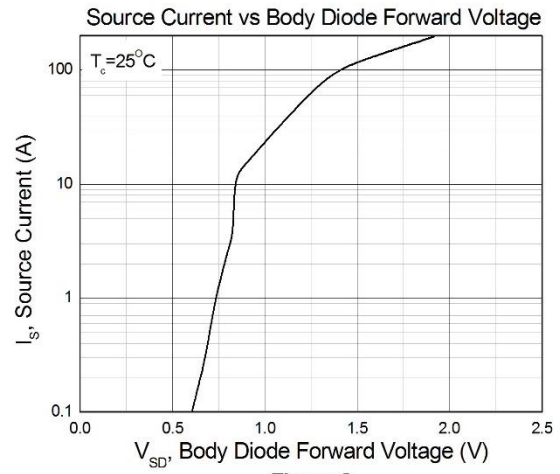


Figure 8



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### Test Circuits & Waveforms

Figure 9: Gate Charge Test Circuit

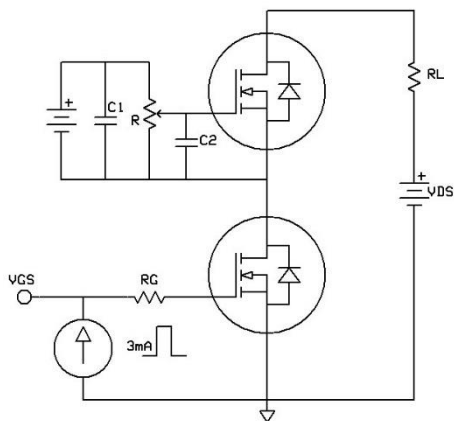


Figure 10: Gate Charge Waveform

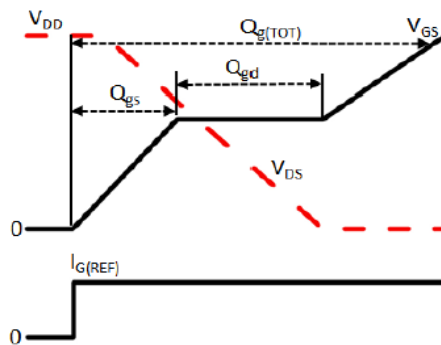


Figure 11: Switching Time Test Circuit

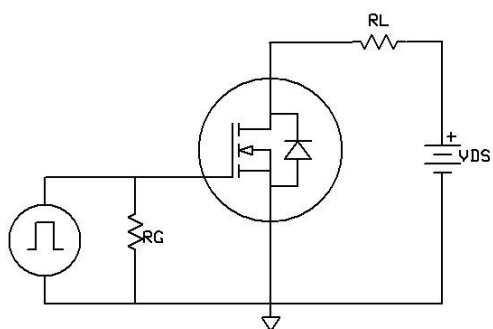
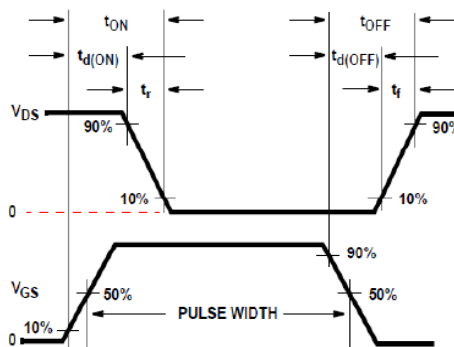


Figure 12: Switching Time Waveform

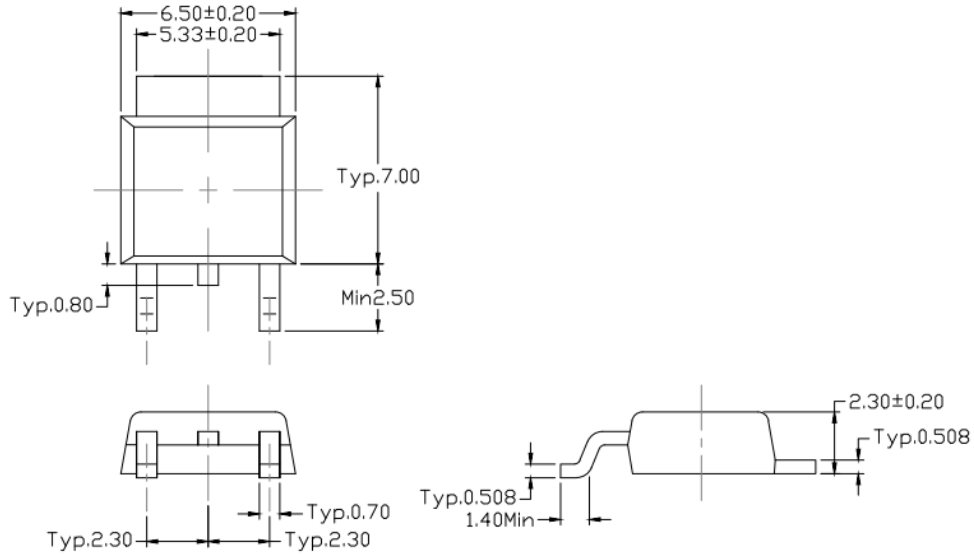




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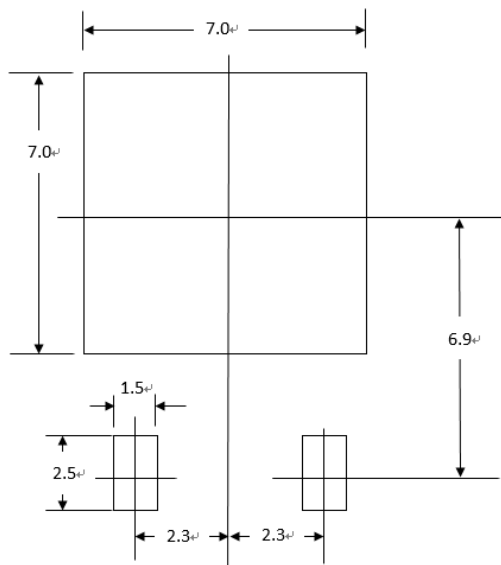
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### Package Dimension (TO-252)



Dimensions in mm unless otherwise stated

### Recommended pad layout for surface mount leadform



Dimensions in mm unless otherwise stated

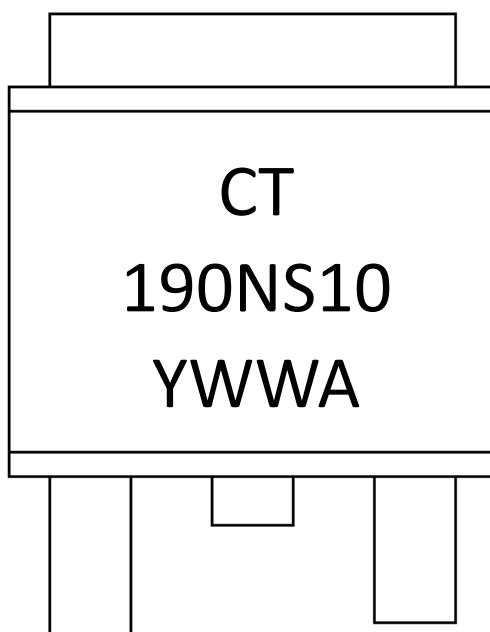




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### Marking Information



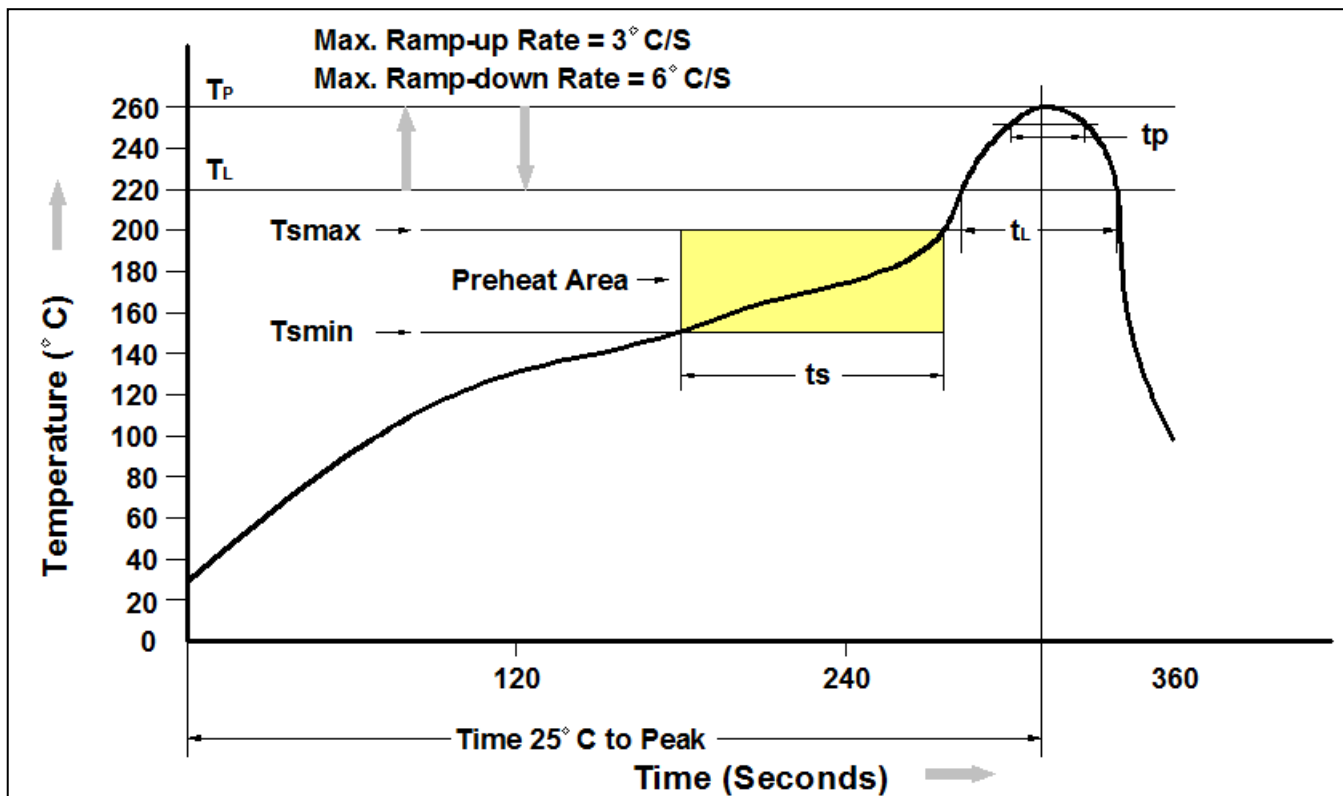
CT : Denotes “CT Micro”  
190NS10 : Device Number  
Y : Fiscal Year  
WW : Work Week  
A : Production Code

### Ordering Information

Part Number	Description	Quantity
CTL190NS10-T52	TO-252 Reel	2500 pcs



Reflow Profile



Profile Feature	Pb-Free Assembly Profile
Temperature Min. (T <sub>smin</sub> )	150°C
Temperature Max. (T <sub>smax</sub> )	200°C
Time (t <sub>s</sub> ) from (T <sub>smin</sub> to T <sub>smax</sub> )	60-120 seconds
Ramp-up Rate (t <sub>L</sub> to t <sub>P</sub> )	3°C/second max.
Liquidous Temperature (T <sub>L</sub> )	217°C
Time (t <sub>L</sub> ) Maintained Above (T <sub>L</sub> )	60 – 150 seconds
Peak Body Package Temperature	260°C +0°C / -5°C
Time (t <sub>P</sub> ) within 5°C of 260°C	30 seconds
Ramp-down Rate (T <sub>P</sub> to T <sub>L</sub> )	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.



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